



STH110N10F7-6 Information



For Reference Only

Part Number STH110N10F7-6
Manufacturer STMicroelectronics

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 110A H2PAK-6 **Package** TO-263-7, D2Pak (6 Leads + Tab)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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STH110N10F7-6 Specifications

| Manufacturer Part Number STHI 10N10F7-6 Manufacturer STMicroelectronics Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-263-7, D2Pak (6 Leads + Tab) Series DeepGATE?, STripFET? VII FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 110A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 72nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5117pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 150W (Tc) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 55A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case TO-263-7, D2Pak (6 Leads + Tab) | | |
|--|--|--------------------------------------|
| Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-263-7, D2Pak (6 Leads + Tab) Series DeepGATE?, STripFET? VII FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 110A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 72nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5117pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 150W (Tc) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 55A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case TO-263-7, D2Pak (6 Leads + Tab) | Manufacturer Part Number | STH110N10F7-6 |
| Package TO-263-7, D2Pak (6 Leads + Tab) Series DeepGATE?, STripFET? VII FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 110A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 72nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5117pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 150W (Tc) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 55A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case TO-263-7, D2Pak (6 Leads + Tab) | Manufacturer | STMicroelectronics |
| PackageTO-263-7, D2Pak (6 Leads + Tab)SeriesDeepGATE?, STripFET? VIIFET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C110A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 250μAGate Charge (Qg) (Max) @ Vgs72nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5117pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)150W (Tc)Rds On (Max) @ Id, Vgs6.5 mOhm @ 55A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageH2PAKPackage / CaseTO-263-7, D2Pak (6 Leads + Tab) | Category | Discrete Semiconductor Products |
| SeriesDeepGATE?, STripFET? VIIFET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C110A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5 V @ 250μAGate Charge (Qg) (Max) @ Vgs72nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5117pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)150W (Tc)Rds On (Max) @ Id, Vgs6.5 mOhm @ 55A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageH2PAKPackage / CaseTO-263-7, D2Pak (6 Leads + Tab) | | Transistors - FETs, MOSFETs - Single |
| FET Type N-Channel Technology MOSFET (Metal Oxide) 100V Current - Continuous Drain (Id) @ 25°C 110A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 117pF @ 50V Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Continuous Drain (Id) @ 25°C 110A (Tc) 1 | Package | TO-263-7, D2Pak (6 Leads + Tab) |
| TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C110A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 250μAGate Charge (Qg) (Max) @ Vgs72nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5117pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)150W (Tc)Rds On (Max) @ Id, Vgs6.5 mOhm @ 55A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageH2PAKPackage / CaseTO-263-7, D2Pak (6 Leads + Tab) | Series | DeepGATE?, STripFET? VII |
| Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C110A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 250μAGate Charge (Qg) (Max) @ Vgs72nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5117pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)150W (Tc)Rds On (Max) @ Id, Vgs6.5 mOhm @ 55A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageH2PAKPackage / CaseTO-263-7, D2Pak (6 Leads + Tab) | FET Type | N-Channel |
| Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 72nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5117pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 55A, 10V Operating Temperature Four Device Package H2PAK Package / Case 10A (Tc) 10A (Tc) 10V 10V 10V 6.5 mOhm 6.5 | Technology | MOSFET (Metal Oxide) |
| Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 250μAGate Charge (Qg) (Max) @ Vgs72nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5117pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)150W (Tc)Rds On (Max) @ Id, Vgs6.5 mOhm @ 55A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageH2PAKPackage / CaseTO-263-7, D2Pak (6 Leads + Tab) | Drain to Source Voltage (Vdss) | 100V |
| Vgs(th) (Max) @ Id 4.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 72nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5117pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 150W (Tc) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 55A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case TO-263-7, D2Pak (6 Leads + Tab) | Current - Continuous Drain (Id) @ 25°C | 110A (Tc) |
| Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 5117pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 55A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case TO-263-7, D2Pak (6 Leads + Tab) | Drive Voltage (Max Rds On, Min Rds On) | 10V |
| Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 55A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case TO-263-7, D2Pak (6 Leads + Tab) | Vgs(th) (Max) @ Id | 4.5V @ 250μA |
| Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 150W (Tc) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 55A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case TO-263-7, D2Pak (6 Leads + Tab) | Gate Charge (Qg) (Max) @ Vgs | 72nC @ 10V |
| FET Feature - 150W (Tc) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 55A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case TO-263-7, D2Pak (6 Leads + Tab) | Input Capacitance (Ciss) (Max) @ Vds | 5117pF @ 50V |
| Power Dissipation (Max) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 55A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case TO-263-7, D2Pak (6 Leads + Tab) | Vgs (Max) | ±20V |
| Rds On (Max) @ Id, Vgs6.5 mOhm @ 55A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageH2PAKPackage / CaseTO-263-7, D2Pak (6 Leads + Tab) | FET Feature | - |
| Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case TO-263-7, D2Pak (6 Leads + Tab) | Power Dissipation (Max) | 150W (Tc) |
| Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case TO-263-7, D2Pak (6 Leads + Tab) | Rds On (Max) @ Id, Vgs | 6.5 mOhm @ 55A, 10V |
| Supplier Device Package H2PAK Package / Case TO-263-7, D2Pak (6 Leads + Tab) | Operating Temperature | -55°C ~ 175°C (TJ) |
| Package / Case TO-263-7, D2Pak (6 Leads + Tab) | Mounting Type | Surface Mount |
| | Supplier Device Package | H2PAK |
| Report errors? | Package / Case | TO-263-7, D2Pak (6 Leads + Tab) |
| | | Report errors? |

STH110N10F7-6 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

STH110N10F7-6 Payment Methods





















STH110N10F7-6 Shipping Methods













If you have any question about STH110N10F7-6, please do not hesitate to contact us!

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